

PLASTIC SILICON RECTIFIER

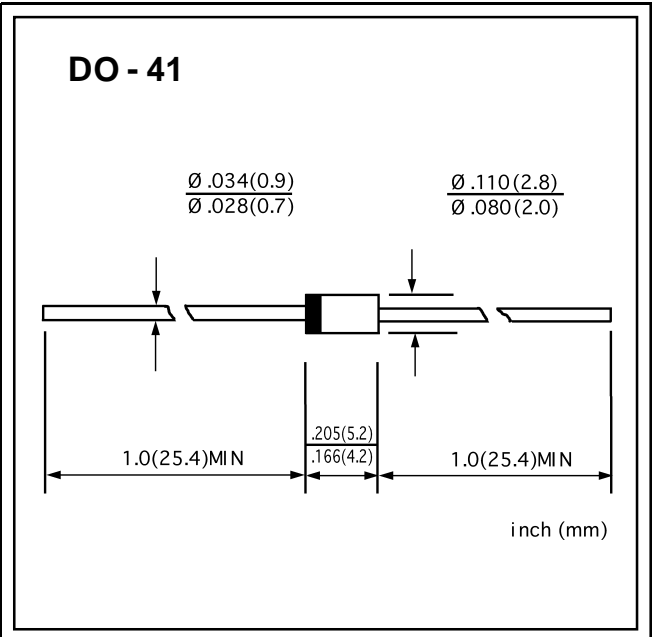
VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 1.0 A

FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon, Alcohol, Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO-41, molded plastic
- ◇ Terminals: Axial lead, solderable per MIL-STD-202, Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.012 ounces, 0.34 grams
- ◇ Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		ERB12 -01	ERB12 -02	ERA12 -04	ERB12 -06	ERB12 -10	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	1000	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	1.0					A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @ $T_J=125^\circ C$	I_{FSM}	60.0					A
Maximum instantaneous forward voltage @ 1.0 A	V_F	1.1					V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	5.0 50.0					μA
Typical junction capacitance (Note1)	C_J	15					pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	50					$^\circ C/W$
Operating junction temperature range	T_J	- 55 --- + 150					$^\circ C$
Storage temperature range	T_{STG}	- 55 --- +150					$^\circ C$

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

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2. Thermal resistance from junction to ambient.

FIG.1 – TYPICAL FORWARD CHARACTERISTIC

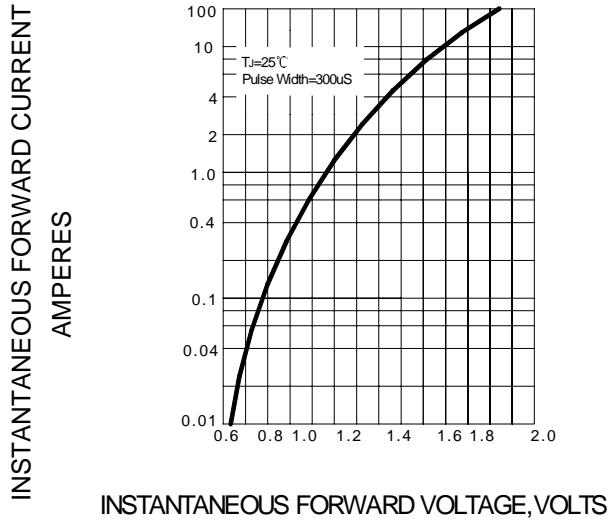


FIG.2 – TYPICAL JUNCTION CAPACITANCE

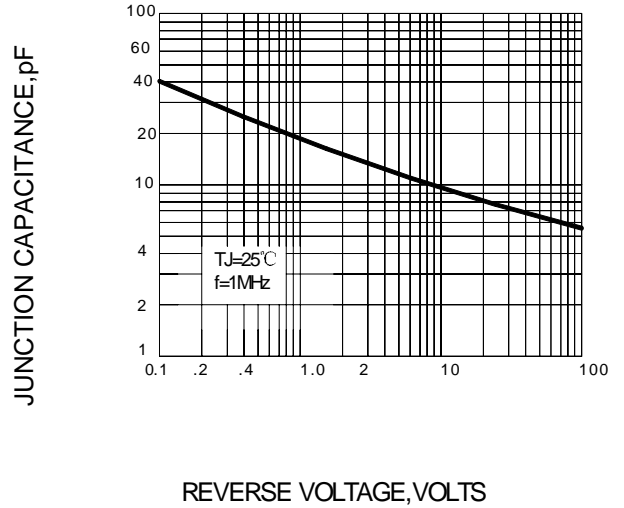


FIG.3 – PEAK FORWARD SURGE CURRENT

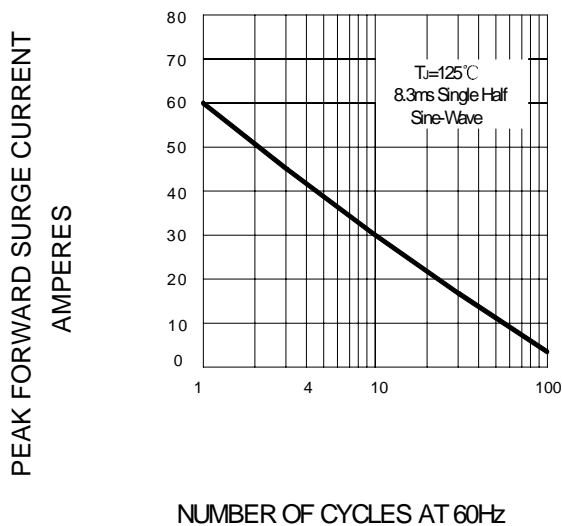


FIG.4 – FORWARD DERATING CURVE

